ABSTRACT OF DISCLOSURE

An etching apparatus and method of etching, the etching apparatus comprises a gas injector injecting reaction gas into a chamber in which semiconductor wafer is accommodated. The gas injector comprises at least a pair of gas suppliers having a gas supplying hole and a gas distributor having a loop-typed upper partition wall protruding from a central zone of an upper side of a plate, and a loop-typed bottom partition wall protruding from a central zone of a bottom side of the plate. A showerhead is disposed having a gap with the gas distributor, and injecting the reaction gas into the chamber. The etching apparatus independently controls an amount of reaction gas injected into a central zone and an edge zone of a chamber when the reaction gas is injected into the chamber, thereby controlling uniformity of density of plasma, deposition speed, etching speed, and the like in the etching process.